

## NCE N-Channel Super Trench II Power MOSFET

### Description

The NCEP018N60GU uses **Super Trench II** technology that is uniquely optimized to provide the most efficient high frequency switching performance. Both conduction and switching power losses are minimized due to an extremely low combination of  $R_{DS(on)}$  and  $Q_g$ . This device is ideal for high-frequency switching and synchronous rectification.

### Application

- DC/DC Converter
- Ideal for high-frequency switching and synchronous rectification

### General Features

- $V_{DS} = 60V, I_D = 195A$   
 $R_{DS(on)} = 1.5 m\Omega$  (typical) @  $V_{GS} = 10V$
- Excellent gate charge x  $R_{DS(on)}$  product(FOM)
- Very low on-resistance  $R_{DS(on)}$
- 150 °C operating temperature
- Pb-free lead plating

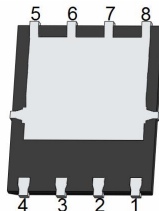
**100% UIS TESTED!**

**100%  $\Delta V_{ds}$  TESTED!**

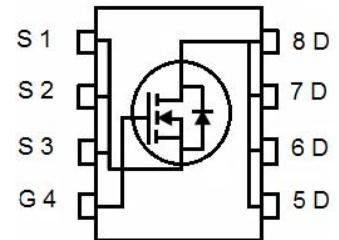
**DFN 5X6-8L**



**Top View**



**Bottom View**



**Schematic Diagram**

### Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
P018N60GU	NCEP018N60GU	DFN5X6-8L	-	-	-

### Absolute Maximum Ratings ( $T_c = 25^\circ C$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	$V_{DS}$	60	V
Gate-Source Voltage	$V_{GS}$	$\pm 20$	V
Drain Current-Continuous	$I_D$	195	A
Drain Current-Continuous( $T_c = 100^\circ C$ )	$I_D(100^\circ C)$	135	A
Pulsed Drain Current	$I_{DM}$	780	A
Maximum Power Dissipation	$P_D$	220	W
Derating factor		1.76	W/ $^\circ C$
Single pulse avalanche energy (Note 1)	$E_{AS}$	871	mJ
Operating Junction and Storage Temperature Range	$T_J, T_{STG}$	-55 To 150	$^\circ C$

### Thermal Characteristic

Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	0.57	$^\circ C/W$
Thermal Resistance, Junction-to-Ambient (Note 4)	$R_{\theta JA}$	50	$^\circ C/W$

## Electrical Characteristics (T<sub>c</sub>=25°C unless otherwise noted)

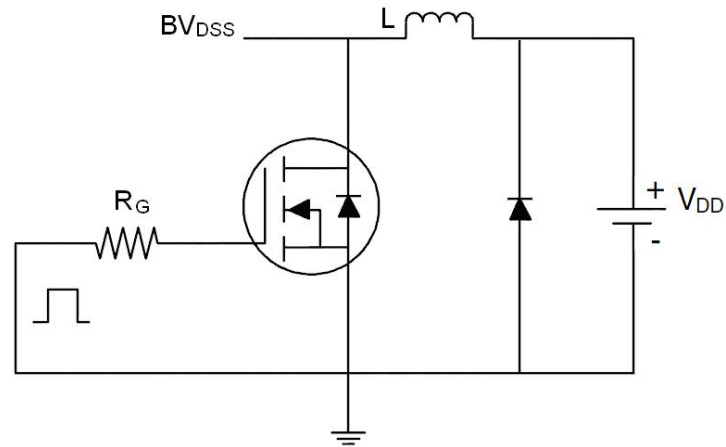
Parameter	Symbol	Condition	Min	Typ	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V I <sub>D</sub> =250μA	60		-	V
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =60V,V <sub>GS</sub> =0V	-	-	1	μA
Gate-Body Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> =±20V,V <sub>DS</sub> =0V	-	-	±100	nA
On Characteristics						
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =V <sub>GS</sub> ,I <sub>D</sub> =250μA	2.0	3.0	4.0	V
Drain-Source On-State Resistance	R <sub>DS(ON)</sub>	V <sub>GS</sub> =10V, I <sub>D</sub> =20A	-	1.5	1.8	mΩ
Forward Transconductance	g <sub>FS</sub>	V <sub>DS</sub> =5V,I <sub>D</sub> =20A	-	50	-	S
Dynamic Characteristics						
Input Capacitance	C <sub>iss</sub>	V <sub>DS</sub> =30V,V <sub>GS</sub> =0V, F=1.0MHz	-	5200	-	PF
Output Capacitance	C <sub>oss</sub>		-	960	-	PF
Reverse Transfer Capacitance	C <sub>rss</sub>		-	65	-	PF
Switching Characteristics (Note 2)						
Turn-on Delay Time	t <sub>d(on)</sub>	V <sub>DD</sub> =30V,I <sub>D</sub> =20A V <sub>GS</sub> =10V,R <sub>G</sub> =4.7Ω	-	17	-	nS
Turn-on Rise Time	t <sub>r</sub>		-	10	-	nS
Turn-Off Delay Time	t <sub>d(off)</sub>		-	60	-	nS
Turn-Off Fall Time	t <sub>f</sub>		-	18	-	nS
Total Gate Charge	Q <sub>g</sub>	V <sub>DS</sub> =30V,I <sub>D</sub> =20A, V <sub>GS</sub> =10V	-	79		nC
Gate-Source Charge	Q <sub>gs</sub>		-	25.5		nC
Gate-Drain Charge	Q <sub>gd</sub>		-	16		nC
Drain-Source Diode Characteristics						
Diode Forward Voltage	V <sub>SD</sub>	V <sub>GS</sub> =0V,I <sub>S</sub> =20A	-		1.2	V
Diode Forward Current	I <sub>S</sub>		-	-	195	A
Reverse Recovery Time	t <sub>rr</sub>	T <sub>J</sub> = 25°C, I <sub>F</sub> = I <sub>S</sub>	-	60		nS
Reverse Recovery Charge	Q <sub>rr</sub>	di/dt = 100A/μs	-	85		nC

### Notes:

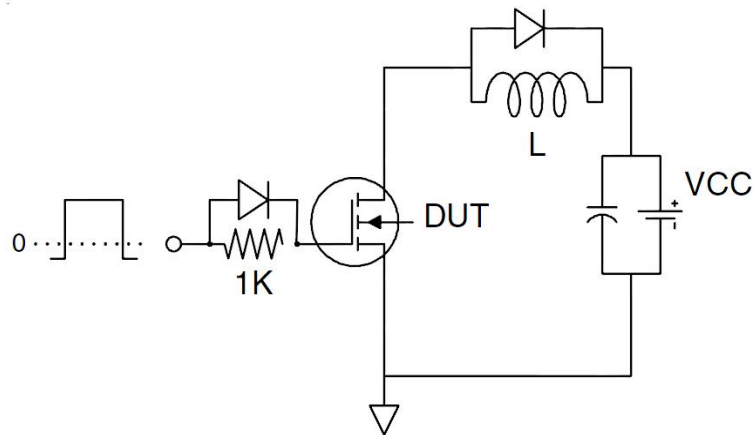
1. EAS condition : T<sub>J</sub>=25°C, V<sub>DD</sub>=30V, V<sub>G</sub>=10V, L=0.5mH, R<sub>G</sub>=25Ω
2. Guaranteed by design, not subject to production
3. These curves are based on the junction-to-case thermal impedance which is measured with the device mounted to a large heatsink, assuming a maximum junction temperature of T<sub>J</sub>(MAX)=150°C. The SOA curve provides a single pulse rating.
4. The value of R<sub>θJA</sub> is measured with the device mounted on 1in<sup>2</sup> FR-4 board with 2oz. Copper, in a still air environment with T<sub>A</sub> =25° C. The maximum allowed junction temperature of 150° C. The value in any given application depends on the user's specific board design.

## Test Circuit

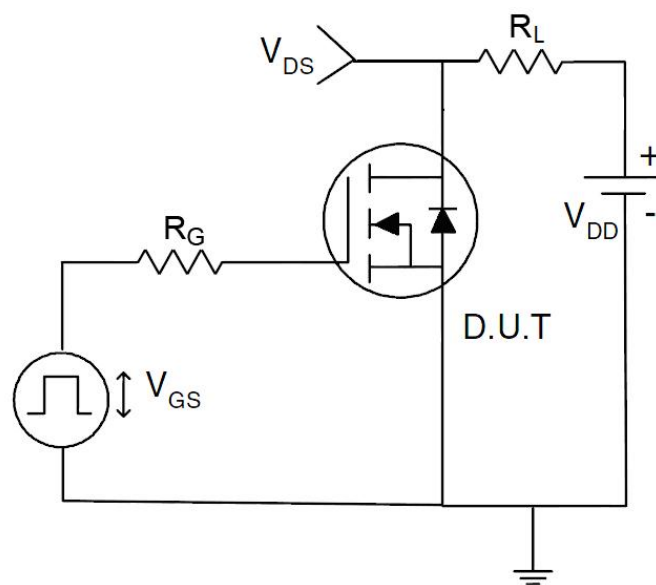
### 1) $E_{AS}$ test Circuit



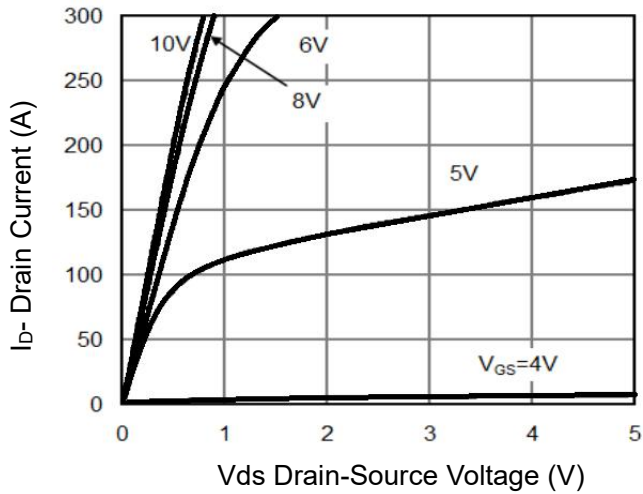
### 2) Gate charge test Circuit



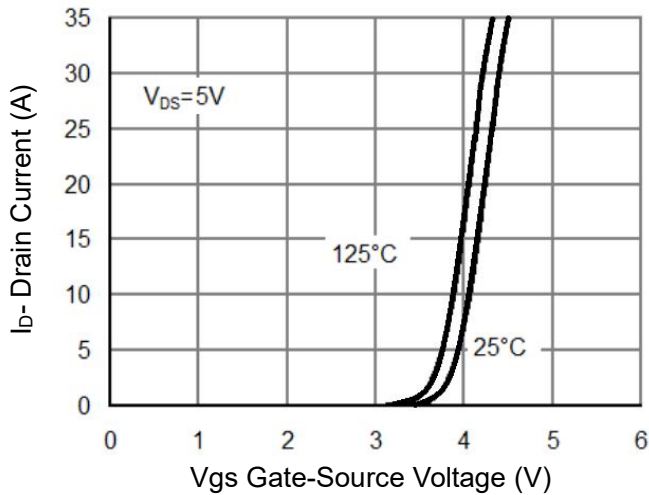
### 3) Switch Time Test Circuit



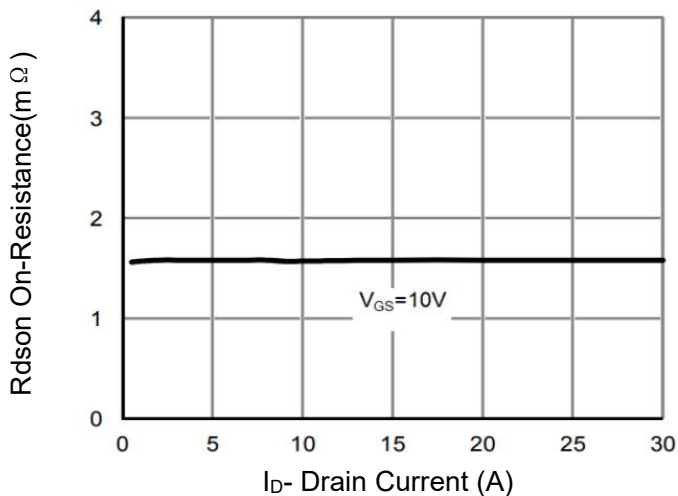
## Typical Electrical and Thermal Characteristics



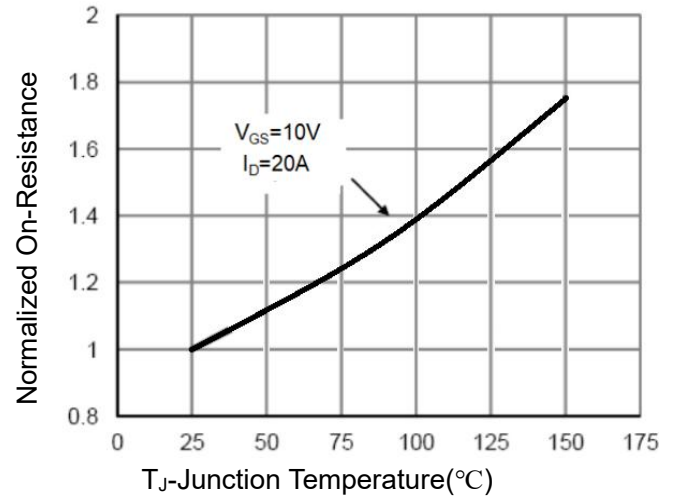
**Figure 1 Output Characteristics**



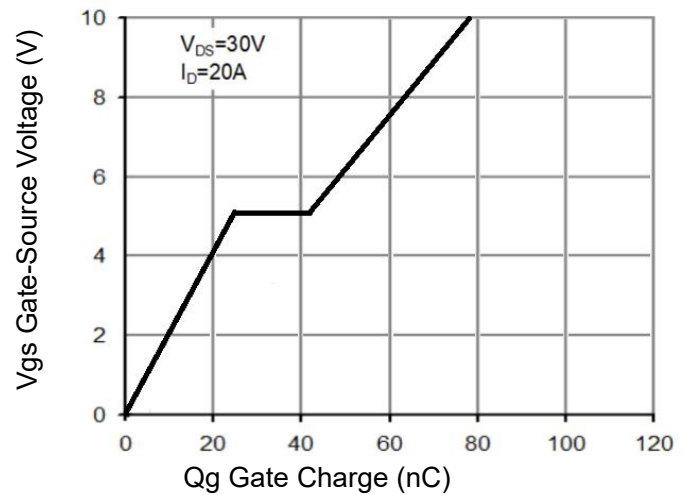
**Figure 2 Transfer Characteristics**



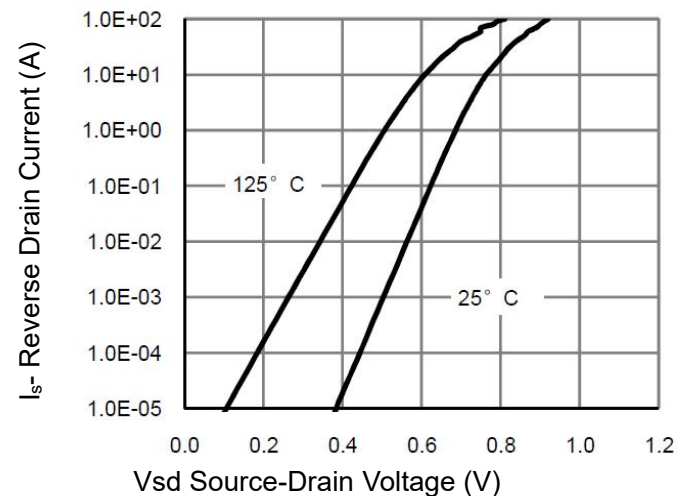
**Figure 3 Rdson- Drain Current**



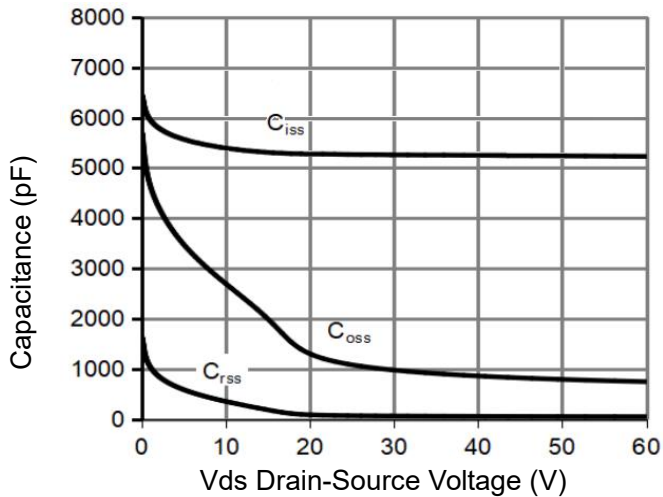
**Figure 4 Rdson-Junction Temperature**



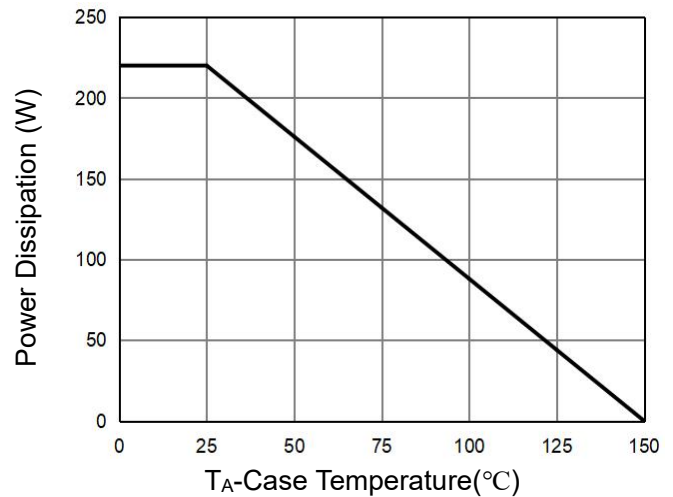
**Figure 5 Gate Charge**



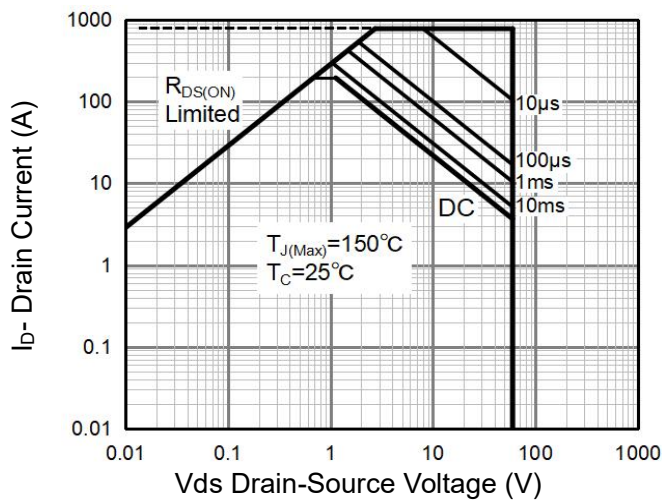
**Figure 6 Source- Drain Diode Forward**



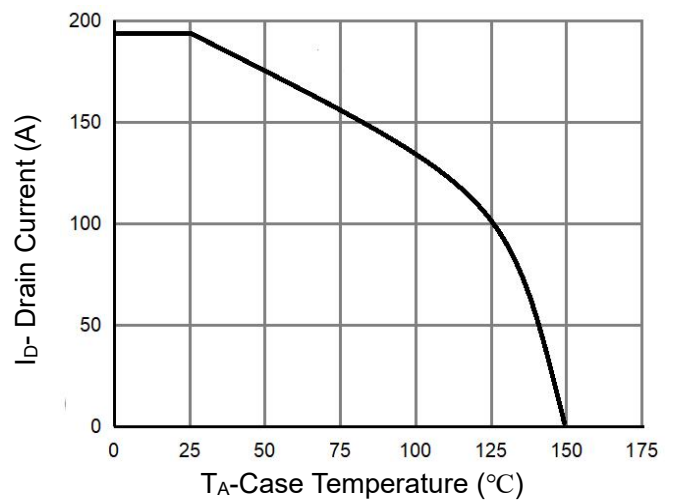
**Figure 7 Capacitance vs Vds**



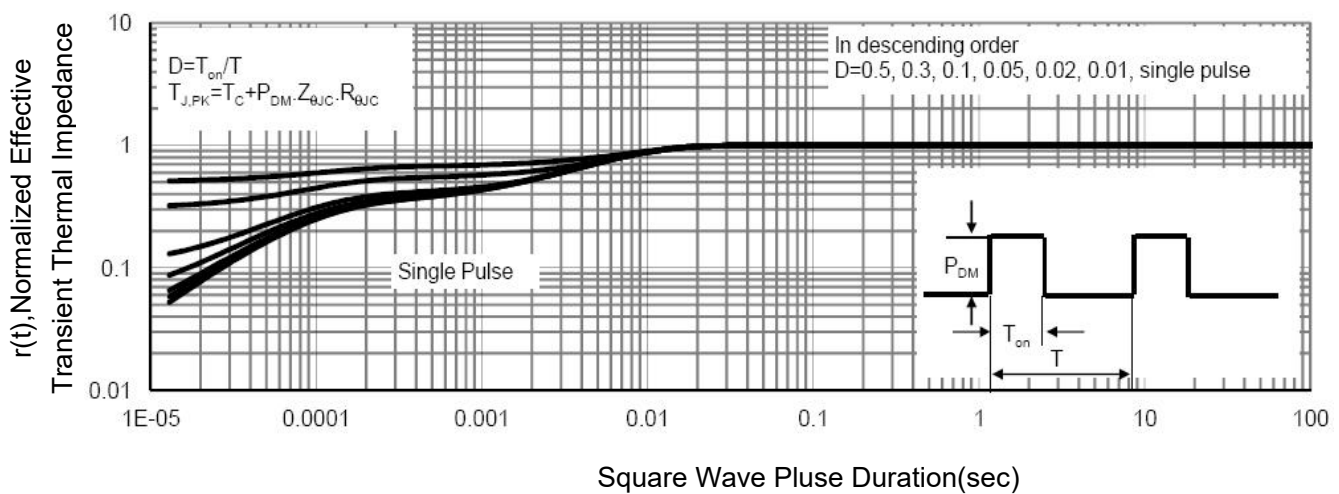
**Figure 9 Power De-rating**



**Figure 8 Safe Operation Area** (Note 3)

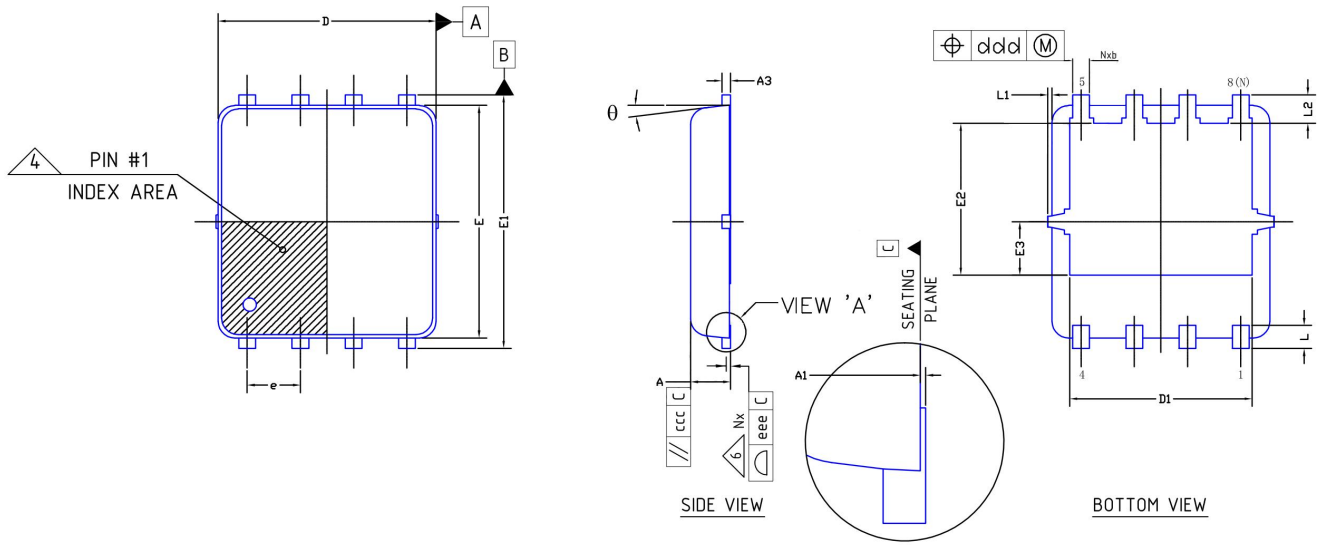


**Figure 10 Current De-rating**



**Figure 11 Normalized Maximum Transient Thermal Impedance**

## DFN5X6-8L Package Information



Dimension Table				
Thickness Symbol	V			NOTE
	MINIMUM	NOMINAL	MAXIMUM	
A	0.85	0.95	1.00	
A1	0.00	---	0.05	
A3	---	0.2 Ref	---	
b	0.30	0.40	0.50	
D	5.20 BSC			
E	5.55 BSC			
e	1.27 BSC			
D1	4.25	4.35	4.45	
E1	5.95	6.05	6.15	
E2	3.525	3.625	3.725	
E3	1.175	1.275	1.375	
L	0.45	0.55	0.65	
L1	0	---	0.15	
L2	0.68 REF			
θ	0°	---	10°	
aaa	0.05			
bbb	0.10			
ccc	0.10			
ddd	0.05			
eee	0.08			
N	8			3
ND	4			5
NOTES	1,2			
LF PART NO.	445831/445897			

NOTE:

1. Dimensioning and tolerancing conform to ASME Y14.5-2009.

2. All dimensions are in millimeters.

3. N is the total number of terminals.

4. The location of the marked terminal #1 identifier is within the hatched area.

5. NE refers to the maximum number of terminals E side.

6. Coplanarity applies to the terminals and all other bottom surface metallization.

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